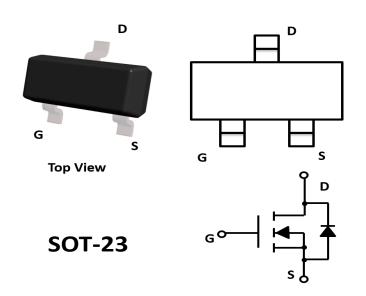


N-Channel Enhancement Mode Field Effect Transistor



Product Summary

 $\begin{array}{lll} \bullet \ V_{DS} & 20V \\ \bullet \ I_D & 3.0A \\ \bullet \ R_{DS(ON)}(\ at \ V_{GS}\!\!=\!\!4.5V) & <52 \ mohm \\ \bullet \ R_{DS(ON)}(\ at \ V_{GS}\!\!=\!\!2.5V) & <80 \ mohm \end{array}$

General Description

- Trench Power LV MOSFET technology
- High Power and current handing capability

Applications

- PWM application
- Load switch

■ Absolute Maximum Ratings (T_A=25 °C unless otherwise noted)

F	arameter	Symbol	Limit	Unit	
Drain-source Voltage		V _{DS}	20	V	
Gate-source Voltage		V_{GS}	±10	V	
Drain Current	T _A =25℃ @ Steady State	1	3.0	Α	
	T _A =70°C @ Steady State	I _D	2.4	Α	
Pulsed Drain Current ^A		I _{DM}	14	А	
Total Power Dissipation @ T _A =	25℃	P _D	0.7	W	
Thermal Resistance Junction-t	o-Ambient @ Steady State ^B	R _{0JA} 178		°C/W	
Junction and Storage Tempera	ture Range	T_{J} , T_{STG}	-55∼+150	°C	

■ Ordering Information (Example)

PREFERED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE	
YJL2302B	F2	2302B.	3000	30000	120000	7" reel	

YJL2302B

■ Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Тур	Max	Units	
Static Parameter							
rain-Source Breakdown Voltage BV _{DSS} V _{GS} = 0V, I _D =250μA		V _{GS} = 0V, I _D =250μA	20			V	
Zero Gate Voltage Drain Current	tage Drain Current I _{DSS} V _{DS} =20V,V _{GS} =0V,T _C =25℃				1	μΑ	
Gate-Body Leakage Current	I _{GSS}	V_{GS} = $\pm 10V$, V_{DS} = $0V$			±100	nA	
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS} , I_D =250 μ A	0.55	0.78	1.1	V	
Otatia Basia Ocurso Oc Basiatana	R _{DS(ON)}	V _{GS} = 4.5V, I _D =3.0A		40	52	mΩ	
Static Drain-Source On-Resistance		V _{GS} = 2.5V, I _D =2.0A		55	80		
Diode Forward Voltage	V_{SD}	I _S =3.0A,V _{GS} =0V			1.2	V	
Maximum Body-Diode Continuous Current	Is				3.0	А	
Dynamic Parameters							
Input Capacitance	C _{iss}			280		pF	
Output Capacitance	C _{oss}	V _{DS} =10V,V _{GS} =0V,f=1MHZ		46			
Reverse Transfer Capacitance	C _{rss}			29			
Switching Parameters							
Total Gate Charge	Q_g			2.9		nC	
Gate Source Charge	Q_{gs}	V _{GS} =4.5V,V _{DS} =10V,I _D =3.0A		0.4			
Gate Drain Charge	Q_gd			0.6			
Turn-on Delay Time	t _{D(on)}			13		- ns	
Turn-on Rise Time	t _r	V _{GS} =4.5V,V _{DD} =10V, R _L =1.5Ω,		54			
Turn-off Delay Time	t _{D(off)}	$R_{GEN}=3\Omega$		18			
Turn-off Fall Time	t _f			11			

A. Pulse Test: Pulse Width \leq 300us, Duty cycle \leq 2%.

B. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.

■ Typical Performance Characteristics

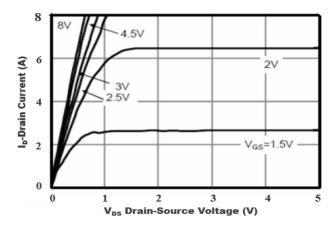


Figure 1. Output Characteristics

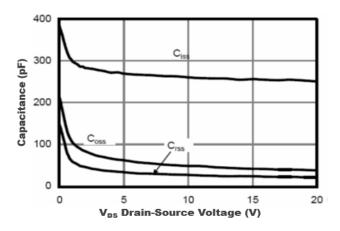


Figure 3. Capacitance Characteristics

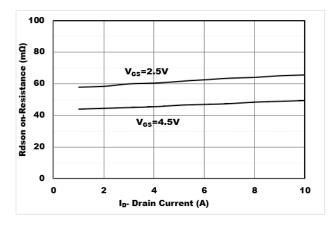


Figure 5. Drain-Source on Resistance

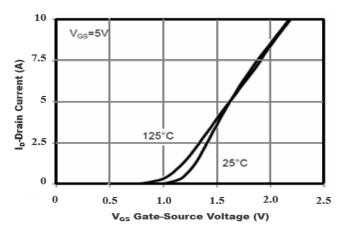


Figure 2. Transfer Characteristics

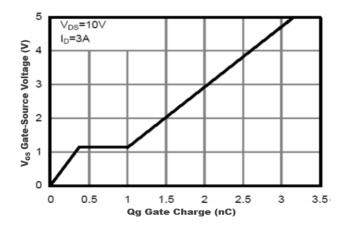


Figure 4. Gate Charge

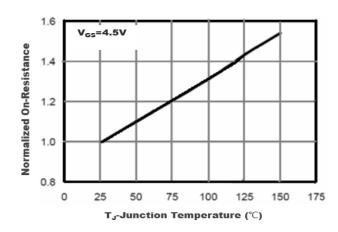


Figure 6. Drain-Source on Resistance

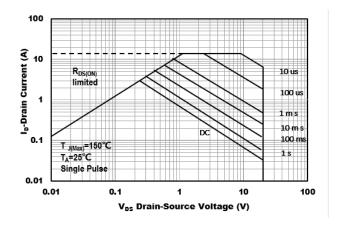


Figure 7. Safe Operation Area

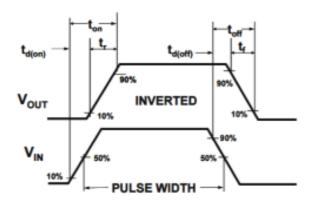
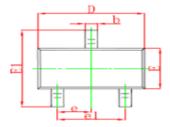
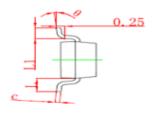
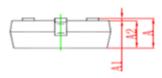


Figure8. Switching wave

■SOT-23 Package information

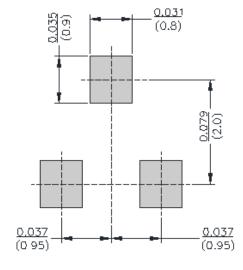






Cumbal	Dimentions	in Millimeter	Dimentions in Inches		
Symbol	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.100	0.200	0.004	0.008	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950Type		0.037Type		
e1	1.800	2.000	0.071	0.079	
L	0.550REF		0.220REF		
L1	0.300	0.500	0.012	0.020	
θ	0 °	8 °	0 °	8 °	

■SOT-23 Suggested Pad Layout



YJL2302B

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